

-17-

LATERAL FET STRUCTURE WITH IMPROVED BLOCKING VOLTAGE AND ON
RESISTANCE PERFORMANCE

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Abstract of the Disclosure

10 In one embodiment, a lateral FET cell is formed in a
body of semiconductor material. The body of semiconductor
material includes alternating layers of opposite
conductivity type that extend between a trench drain region
and a trench gate structure. The trench gate structure
controls at least one sub-surface channel region. The body
of semiconductor material provides sub-surface drift regions
15 to reduce on resistance without increasing device area.